

L Number	Hits	Search Text	DB	Time stamp
-	1	365/158,171.ccls. and cell\$1 and (magnetic adj layer) and (magnetic adj pole\$1) and (demagnetization adj field)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/30 15:04
-	3	365/\$.ccls. and cell\$1 and (magnetic adj layer) and (magnetic adj pole\$1) and (demagnetization adj field)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/30 15:06
-	6	365/\$.ccls. and cell\$1 and (magnetic near2 layer) and (magnetic near2 pole\$1) and (demagnetization near2 field)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/30 15:10
-	2	365/\$.ccls. and cell\$1 and (magnetic near2 layer) and (free near2 magnetic near2 pole\$1) and (demagnetization near2 field)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/30 15:11
-	2	cell\$1 and (magnetic near2 layer) and (free near2 magnetic near2 pole\$1) and (demagnetization near2 field) and (magnetic near2 flux)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/30 15:12
-	13	cell\$1 and (magnetic near2 layer) and (magnetic near2 pole\$1) and (demagnetization near2 field) and (magnetic near2 flux)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/30 15:18
-	363	cell\$1 with (magnetic near2 memory near2 device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/30 15:19
-	138	365/171,158.ccls. and cell\$1 with (magnetic near2 memory near2 device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 17:10
-	25	magnetic with layer and (free near2 pole\$1) and demagnetization and flux	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/30 15:21
-	2	365/171,158.ccls. and cell\$1 with (magnetic near2 memory near2 device) and pole\$1 and flux and demagnetization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/30 15:28
-	1	365/\$.ccls. and (bit near2 cell\$1) and (magnetic near2 layer) and (free near2 magnetic near2 pole\$1) and (demagnetization near2 field)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 15:54
-	27	365/\$.ccls. and cell\$1 near2 (CS or "chip select") same level\$1 and signal\$1 and register	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 17:25
-	31	cell\$1 near2 (CS or "chip select") same level\$1 and signal\$1 and register	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 17:57
-	1656	configur\$5 same (CS or "chip select") and register	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 17:58

-	238	365/.ccls. and configur\$5 same (CS or "chip select") and register	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 17:58
-	201	365/.ccls. and configur\$5 same (CS or "chip select") and level\$1 and signal\$1 and register	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 17:59
-	36	365/.ccls. and configur\$5 same (CS or "chip select") with level\$1 and signal\$1 and register	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 18:07
-	2	(memory near cell) and (flux with absorb\$3 with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/03 06:00
-	14	(memory near cell) and (absorb\$3 with layer) and flux	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/03 06:02
-	7	365/.ccls. and (magnetic near3 junction and (permeabi\$4 with "100"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/03 06:11
-	40	365/.ccls. and (magnetic near3 memory near3 array)and (coer\$7 with (smaller or less))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/03 06:17
-	36	365/158,171,173,189.01,230.06,55,66,213.cc and (magnetic near3 memory near3 array) and (flux with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/03 06:19
-	52	365/158,171,173,189.01,230.06,55,66,213.cc and (magnetic near3 junction) and (flux with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/03 06:24